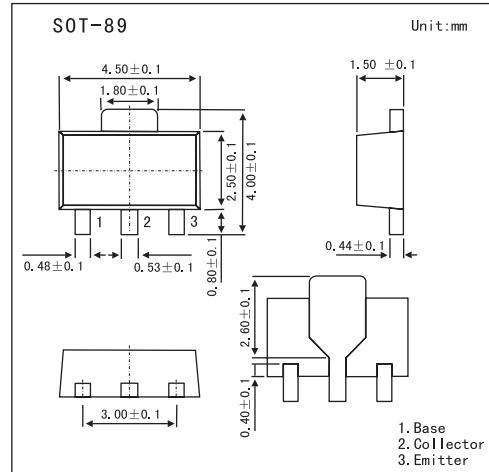


## FCX1151A

### ■ Features

- 2W power dissipation.
  - 5A peak pulse current.
  - Excellent HFE characteristics up to 5 Amps.
  - Extremely low saturation voltage E.g. 60mV Typ.
  - Extremely low equivalent on-resistance.
- R<sub>CE(sat)</sub> 66mΩ at 3A.



### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	-45	V
Collector-emitter voltage	V <sub>C EO</sub>	-40	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Continuous collector current	I <sub>CM</sub>	-5	A
Peak pulse current *3	I <sub>C</sub>	-3	A
Base current	I <sub>B</sub>	-500	mA
Power dissipation	P <sub>tot</sub>	1 *1	W
		2 *2	W
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to +150	°C

\*1 recommended P<sub>tot</sub> calculated using FR4 measuring 15X15X0.6mm

\*2 Maximum power dissipation is calculated assuming that the device is mounted on FR4 substrate measuring 40X40X0.6mm

\*3 Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤2%

**FCX1151A**

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>c</sub> =-100µA	-45			V
Collector-emitter breakdown voltage *	V <sub>(BR)CEO</sub>	I <sub>c</sub> =-10mA	-40			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>e</sub> =-100µA	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-36V		-0.3	-100	nA
Collector Emitter Cut-Off Current	I <sub>CES</sub>	V <sub>CE</sub> =-32V		-0.3	-100	nA
Emitter Cut-Off Current	I <sub>EBO</sub>	V <sub>EB</sub> =-4V		-0.3	-100	nA
Collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	I <sub>c</sub> =-0.1A, I <sub>b</sub> =-1mA I <sub>c</sub> =-0.5A, I <sub>b</sub> =-5mA I <sub>c</sub> =-1A, I <sub>b</sub> =-20mA I <sub>c</sub> =-3A, I <sub>b</sub> =-250mA		-60 -120 -140 -200	-90 -180 -220 -300	mV
Base-emitter saturation voltage *	V <sub>BE(sat)</sub>	I <sub>c</sub> =-3A, I <sub>b</sub> =-250mA		-985	-1050	mV
Base-emitter ON voltage *	V <sub>BE(on)</sub>	I <sub>c</sub> =-3A, V <sub>CE</sub> =-2V		-850	-950	mV
Static Forward Current Transfer Ratio *	h <sub>FE</sub>	I <sub>c</sub> =-10mA, V <sub>CE</sub> =-2V I <sub>c</sub> =-0.5A, V <sub>CE</sub> =-2V I <sub>c</sub> =-2A, V <sub>CE</sub> =-2V I <sub>c</sub> =-3A, V <sub>CE</sub> =-2V I <sub>c</sub> =-5A, V <sub>CE</sub> =-2V	270 250 180 100	450 400 300 190 45	800	
Transitional frequency	f <sub>T</sub>	I <sub>c</sub> =-50mA, V <sub>CE</sub> =-10V, f=50MHz		145		MHz
Output capacitance	C <sub>obo</sub>	V <sub>CB</sub> =-10V, f=1MHz		40		pF
Turn-on time	t <sub>(on)</sub>	I <sub>c</sub> =-2A, V <sub>CC</sub> =-30V		170		ns
Turn-off time	t <sub>(off)</sub>	I <sub>B1</sub> =I <sub>B2</sub> =-20mA		460		ns

\* Pulse test: tp = 300 µs; d ≤ 0.02.

## ■ Marking

Marking	151
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